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INTERNATIONAL APPLICATION NO.	INTERNATIONAL FILING DATE	PRIORITY DATE CLAIMED
PCT/JP00/07239	OCTOBER 16, 2000	NOVEMBER 16, 1999
TITLE OF INVENTION		
ACOUSTIC WAVE APPARATUS		
APPLICANT(S) FOR DO/EO/US		
YOSHIDA, Kenji; WADAKA, Shusou; MISU, Koichiro; NAGATSUKA, Tsutomu; MURAI, Kouji; YAMAGUCHI, Masatsune; HASHIMOTO, Kenya; OHMORI, Tatsuya; IBATA, Koji		
Applicant herewith submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:		
<p>1. <input checked="" type="checkbox"/> This is a FIRST submission of items concerning a filing under 35 U.S.C. 371.</p> <p>2. <input type="checkbox"/> This is a SECOND or SUBSEQUENT submission of items concerning a filing under 35 U.S.C. 371.</p> <p>3. <input checked="" type="checkbox"/> This express request to begin national examination procedures (35 U.S.C. 371(f)) at any time rather than delay examination until the expiration of the applicable time limit set in 35 U.S.C. 371(b) and PCT Articles 22 and 39 (1).</p> <p>4. <input type="checkbox"/> The US has been elected by the expiration of 19 months from the priority date (Article 31).</p> <p>5. <input checked="" type="checkbox"/> A copy of the International Application as filed (35 U.S.C. 371(c)(2))</p> <p style="margin-left: 20px;"> <input checked="" type="checkbox"/> is transmitted herewith (required only if not transmitted by the International Bureau). WO 01/37426 <input type="checkbox"/> has been transmitted by the International Bureau. <input type="checkbox"/> is not required, as the application was filed in the United States Receiving Office (RO/US). </p> <p>6. <input checked="" type="checkbox"/> An English language translation of the International Application as filed (35 U.S.C. 371(c)(2)).</p> <p style="margin-left: 20px;"> <input checked="" type="checkbox"/> is transmitted herewith. <input type="checkbox"/> has been previously submitted under 35 U.S.C. 154(d)(4) </p> <p>7. <input checked="" type="checkbox"/> Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371(c)(3)).</p> <p style="margin-left: 20px;"> <input type="checkbox"/> are transmitted herewith (required only if not transmitted by the International Bureau). <input type="checkbox"/> have been transmitted by the International Bureau. <input type="checkbox"/> have not been made; however, the time limit for making such amendments has NOT expired. <input checked="" type="checkbox"/> have not been made and will not be made. </p> <p>8. <input type="checkbox"/> An English language translation of the amendments to the claims under PCT Article 19 (35 U.S.C. 371(c)(3)).</p> <p>9. <input checked="" type="checkbox"/> An oath or declaration of the inventor(s) (35 U.S.C. 371(c)(4)). (Original)</p> <p>10. <input type="checkbox"/> An English language translation of the annexes of the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. 371(c)(5)).</p>		
Items 11. to 20. below concern document(s) or information included:		
<p>11. <input checked="" type="checkbox"/> An Information Disclosure Statement under 37 CFR 1.97 and 1.98./International Search Report (PCT/ISA/210) with 13 documents</p> <p>12. <input checked="" type="checkbox"/> An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included.</p> <p>13. <input checked="" type="checkbox"/> A FIRST preliminary amendment.</p> <p>14. <input type="checkbox"/> A SECOND or SUBSEQUENT preliminary amendment.</p> <p>15. <input type="checkbox"/> A substitute specification.</p> <p>16. <input type="checkbox"/> A change of power of attorney and/or address letter.</p> <p>17. <input type="checkbox"/> A computer-readable form of the sequence listing in accordance with PCT Rule 13ter.2 and 35 U.S.C. 1.821-1.825.</p> <p>18. <input type="checkbox"/> A second copy of the published international application under 35 U.S.C. 154(d)(4).</p> <p>19. <input type="checkbox"/> A second copy of the English language translation of the international application under 35 U.S.C. 154(d)(4).</p> <p>20. <input checked="" type="checkbox"/> Other items or information: I., SEVEN (7) Sheets Formal Drawings </p>		

PATENT
1163-0345P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: YOSHIDA, Kenji et al Conf.:
Int'l. Appl. No.: PCT/JP00/07239
Appl. No.: NEW Group:
Filed: July 16, 2001 Examiner:
For: ACOUSTIC WAVE APPARATUS

PRELIMINARY AMENDMENT**BOX PATENT APPLICATION**Assistant Commissioner for Patents
Washington, DC 20231

July 16, 2001

Sir:

The following Preliminary Amendments and Remarks are respectfully submitted in connection with the above-identified application.

AMENDMENTSIN THE SPECIFICATION:

Please amend the specification as follows:

Before line 1, insert --This application is the national phase under 35 U.S.C. § 371 of PCT International Application No. PCT/JP00/07239 which has an International filing date of October 18, 2000, which designated the United States of America and was not published in English.

REMARKS

The specification has been amended to provide a cross-reference to the previously filed International Application.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

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ACOUSTIC WAVE APPARATUS

This application is the national phase under 35 U.S.C. § 371 of PCT International Application No. PCT/JP00/07239 which has an International filing date of October 18, 2000, which designated the United States of America and was not published in English.

BACKGROUND OF THE INVENTION

Technical Field

The present invention relates to an acoustic wave apparatus for propagating acoustic waves, used for the circuit of a communication equipment, an electronic device or the like.

Background Art

Heretofore, in such an acoustic wave apparatus in which a piezoelectric substrate containing tantalum acid lithium (LiTaO_3 , referred to as LT hereinafter) has been used, the cut angle θ of the LT substrate has been set equal to 36° . This setting was a result of the calculation that if an electrode was formed on the surface of such a substrate, and the substrate surface was electrically short-circuited, the amount of propagation loss would be reduced to nearly a value of zero.

However, such calculation was made by assuming the establishment of an ideal state where the electrode had no thickness. Consequently, in the actual acoustic wave apparatus comprising an electrode having thickness, there was a possibility that a condition for reducing the amount of propagation loss to a minimum may be different. In addition, the calculation was made by examining the case where the entire surface of the substrate was covered with the electrode. Consequently, in the acoustic wave apparatus comprising electrode fingers cyclically arrayed as in the case of an SAW filter, there was a possibility

that a condition for reducing the amount of propagation loss to a minimum might be different.

Thus, in Japanese Patent Application Laid-Open No. 1997-167936 (referred to as a document 1, hereinafter), a condition for reducing the amount of propagation loss to a minimum is examined by taking into consideration the thickness of a grating electrode formed on the surface of the LT substrate. Fig. 1 shows the result of calculating the amount of propagation loss in a ladder surface acoustic wave filter of the document 1 shown in Fig. 7. In the drawing, an ordinate indicates the amount of loss made when a surface acoustic wave (referred to as SAW, hereinafter) is propagated per wavelength (λ), i.e., the amount of loss per wavelength (dB/ λ). An abscissa indicates a standardized electrode thickness (h/λ), where the thickness h of the electrode is standardized based on the wavelength λ of SAW.

Fig. 1 shows the case where an LT crystal X-axis direction is set as a SAW propagation direction, a surface perpendicular to a " θ -rotated Y" axis obtained by rotating a crystal Y axis by θ around the crystal X axis, is set as a substrate surface, and a cut angle θ is set in the range of 36° to 46° . The LT substrate having the surface perpendicular to the " θ -rotated Y" axis set as its surface and the crystal X-axis direction set as the SAW propagation direction is represented by θ -rotated Y-cut X-propagation tantalum acid lithium, abbreviated to θ YX-LT, or θ YX-LiTaO₃. In many cases, the electrode is made of aluminum (Al) or an alloy mainly containing Al.

As shown in Fig. 1, if a standardized electrode thickness (h/λ) is 0, the amount of loss per wavelength (dB/ λ) is minimum when a cut angle θ is about 36° . This result coincides with that of the conventional calculation, i.e., if the ideal state of the electrode having no thickness is established, the amount of propagation loss is reduced to nearly a value of zero when a cut angle θ is 36° .

In addition, as shown in Fig. 1, if a cut angle θ is 40° , the amount of loss per wavelength (dB/ λ) is minimum when a standardized electrode thickness (h/λ) is about 0.05. If a cut angle θ is 42° , the amount of loss per wavelength (dB/ λ) is minimum when a standardized electrode thickness (h/λ) is about 0.075. Accordingly, in the SAW device realized by setting the standardized electrode thickness (h/λ) in a range above 0.05, a cut angle θ for reducing the amount of propagation loss to a minimum resides in a range above 40° .

As apparent from the foregoing discussion made with reference to Fig. 1, it is possible to reduce the amount of propagation loss to a minimum by selecting the proper combination of a standardized electrode thickness (h/λ) with a cut angle θ . As a result, the insertion loss of the SAW device can be reduced. Therefore, in recent years, the LT substrate having a cut angle θ set equal to 42° has been employed.

There are several kinds of acoustic waves. If a cut angle θ is set in the range of about 36° to 46° , and the direction of propagation is a crystal X axis, for example, a surface skimming bulk wave (SSBW), which is a bulk wave propagated along the surface of an LT substrate described in a document: pp. 158-165, "Journal of Institute of Electronics and Communication Engineers of Japan", Vo 1. J67-C, No. 1, Jan. 1984 (referred to as a document 2, hereinafter), and a leaky surface acoustic wave (LSAW) are propagated. In the present application, these waves are generically termed as SAW, except when the waves are distinguished from each other.

Fig. 2 is an upper surface view showing the constitution of the SAW filter, which is one type of an acoustic wave apparatus. In the drawing, a reference numeral 1 denotes an LT substrate made of a piezoelectric material; 3 an electrode finger; 4 a bonding pad; 5 an input side interdigital transducer (IDT) for performing

electric - surface acoustic wave energy conversion; 6 an output side IDT for performing surface acoustic wave - electric energy conversion; 7 an input terminal; and an 8 an output terminal. W_0 represents a maximum value of the length of a portion intersected by the electrode finger 3.

Fig. 3 is a sectional view of the SAW filter shown in Fig. 2. In the drawing, a code w represents a width of the electrode finger 3; p an arraying cycle of electrode fingers 3; and h a thickness of the electrode finger 3.

Next, the operation of the SAW filter will be described.

An electric signal applied to the input terminal 7 forms an electric field at the intersection of each electrode finger 3 of the input side IDT 5. In this case, as the LT substrate 1 is made of the piezoelectric material, the electric field causes distortion. If the input signal has a frequency f , the strain that has been generated is vibrated at the frequency f , converting the signal into SAW. This SAW is then transmitted in a direction perpendicular to the electrode finger 3. At the output side IDT 6, the SAW is converted back into the electric signal. The conversion of the electric signal into the SAW, and the conversion of the SAW into the electric signal are reversible to each other.

If a cut angle θ is about 36° , and the propagation direction of the SAW is in a crystal X-axis direction, as described in the document 2, the displacement component of the SAW has a direction parallel to the electrode finger 3, and the surface of the LT substrate 1. Such a displacement component depends on the cut angle θ of the cut surface of the LT substrate 1 and the propagation direction of the SAW.

The SAW excited by the input side IDT 5 is propagated toward the output side IDT 6. However, if there is propagation loss in the LT substrate 1, the power of the SAW having reached the output side IDT 6 is smaller than that of the SAW immediately after its excitation by the

input side IDT 5. The amount of the loss is approximately equal to a value obtained by multiplying a distance between the centers of the input side IDT 5 and the output side IDT 6 standardized based on the wavelength λ of the SAW by an attenuation constant α .

Thus, assuming that the distances of the input side IDT 5 and the output side IDT 6 are equal to each other, as the amount of propagation loss in the LT substrate 1 is increased, the amount of insertion loss for the SAW filter is larger. As described in a document: pp. 56 to 81, "Surface Acoustic Wave Engineering", Institute of Electronics and Communication Engineers of Japan, issued by Corona Inc., Nov. 1983, since the wavelength λ of the SAW is double the arraying cycle p of the electrode fingers 3, the amount of loss generated following propagation is approximately equal to a value, which is obtained by multiplying a numerical value half an average value of the numbers of electrode fingers 3 constituting the input side IDT 5 and the output side IDT 6 by an attenuation constant α .

For example, as shown in Fig. 2, assuming that each of the input side IDT 5 and the output side IDT 6 has 7 electrode fingers 3, and the input side IDT 5 and the output side IDT 6 are disposed close to each other, the amount of loss generated following propagation is equal to a value, which is about 3 to 4 times larger than the attenuation constant α . As an example, if an attenuation constant α is 0.02 (dB/ λ), then the amount of loss following propagation takes a value set in the range of 0.06 to 0.08 dB.

As apparent from the foregoing, in order to realize a low-loss SAW device, it is important to use an LT substrate 1 having a small amount of propagation loss. Heretofore, in the acoustic wave apparatus of the foregoing type, a cut angle θ set in a range above 36° has been employed.

As described above, the propagation loss greatly

provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalum acid lithium; and an interdigital transducer including a conductor formed on the substrate. In this case, a surface rotated in the range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as the surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting the interdigital transducer by a wavelength λ of a surface acoustic wave is set in the range of 0.01 to 0.05, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalum acid lithium; and an interdigital transducer including a conductor formed on the substrate. In this case, a surface rotated in the range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as the surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting the interdigital transducer by a wavelength λ of a surface acoustic wave is set in the range of 0.05 to 0.075, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

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Thus, an acoustic wave apparatus with lower loss characteristics and wider band than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalum acid lithium; an interdigital transducer including a conductor formed on the substrate; and a reflector including a conductor formed on the substrate. In this case, a surface rotated in the range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting at least a part of the reflector by a wavelength λ of a surface acoustic wave is set in the range of 0.01 to 0.05, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

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Thus, an acoustic wave apparatus with lower loss

characteristics and wider band characteristics than the conventional apparatus can be realized.

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Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

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Thus, an acoustic wave apparatus with lower loss

characteristics and wider band characteristics than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalic acid lithium; and an interdigital transducer including a conductor formed on the substrate. In this case, a surface rotated in the range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting a part of the interdigital transducer by a wavelength λ of a surface acoustic wave is set in the range of 0.075 to 0.1, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalic acid lithium; an interdigital transducer including a conductor formed on the substrate; and a reflector including a conductor formed on the substrate. In this case, a surface rotated in the range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of the reflector by a wavelength λ of a surface acoustic wave is set in the range of 0.01 to 0.05, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arraying cycle p of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalic acid lithium; an interdigital transducer including a conductor formed on the substrate; and a reflector including a conductor formed on the substrate. In this case, a surface rotated in the range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of the reflector by a wavelength λ of a surface acoustic wave is set in the range of 0.05 to 0.075, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arranging cycle of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

In accordance with the invention, there is provided an acoustic wave apparatus, comprising: a piezoelectric substrate mainly containing tantalic acid lithium; an interdigital transducer including a conductor formed on the substrate; and a reflector including a conductor formed on the substrate. In this case, a surface rotated in the range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of the substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of the reflector by a wavelength λ of a surface acoustic wave is set in the range of 0.075 to 0.1, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arraying

cycle p of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

Thus, an acoustic wave apparatus with lower loss characteristics and wider band characteristics than the conventional apparatus can be realized.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a view showing a result of calculating an attenuation constant, described in Japanese Patent Application Laid-Open No. 1997-167936.

Fig. 2 is an upper surface view showing a constitution of an SAW filter.

Fig. 3 is a sectional view of the SAW filter shown in Fig. 2.

Fig. 4 is a view showing a result of calculating an attenuation constant when a standardized electrode thickness is set equal to 0.01, according to a first embodiment of the present invention.

Fig. 5 is a view showing a result of calculating an electromechanical coupling coefficient when the standardized electrode thickness is equal to 0.01, according to the first embodiment of the invention.

Fig. 6 is a view showing a result of calculating an attenuation constant when a standardized electrode thickness is set equal to 0.05, according to the first embodiment of the invention.

Fig. 7 is a view showing a result of calculating an electromechanical coupling coefficient when the standardized electrode thickness is equal to 0.05, according to the first embodiment of the invention.

Fig. 8 is a view showing a result of calculating an attenuation constant when a standardized electrode thickness is set equal to 0.075, according to the first embodiment of the invention.

Fig. 9 is a view showing a result of calculating an electromechanical coupling coefficient when the

standardized electrode thickness is equal to 0.075, according to the first embodiment of the invention.

Fig. 10 is a view showing a result of calculating an attenuation constant in an LT substrate when a standardized electrode thickness is set equal to 0.1, according to the first embodiment of the invention.

Fig. 11 is a view showing a result of calculating an electromechanical coupling coefficient in the LT substrate when the standardized electrode thickness is equal to 0.1, according to the first embodiment of the invention.

Fig. 12 is a view showing a pattern of a mode-coupled SAW resonant filter.

Fig. 13 is a view showing a result of calculating a minimum insertion loss value of the mode-coupled SAW resonant filter shown in Fig. 12.

Fig. 14 is a view showing a result of calculating feedthrough power of the mode-coupled SAW resonant filter shown in Fig. 12.

BEST MODE FOR CARRYING OUT THE INVENTION

Several embodiments for carrying out best the present invention are now explained in detail with reference to attached drawings.

[First Embodiment]

Fig. 4 is a view showing the result of calculating an attenuation constant α when a standardized electrode thickness (h/λ) is 0.01. In the drawing, an ordinate indicates an attenuation constant α (dB/ λ); and an abscissa a cut angle θ of an LT substrate. As in the case shown in Fig. 1, the crystal X-axis direction of the LT substrate is set as the propagation direction of SAW, and a surface perpendicular to the axis of rotating a crystal Y axis by θ around the crystal X axis, i.e., the surface of rotating the crystal Y axis by θ around the crystal X axis, is set as the surface of the LT substrate.

In the described case, calculation is made as to the propagation characteristic of SAW when electrode fingers each having a width w like that shown in Fig. 3 are endlessly arrayed at an arraying cycle p . Fig. 4 specifically shows the results of calculation made by changing the duty ratio (w/p) of the electrode finger decided based on the width w and the arraying cycle p of the electrode finger from 0.2 to 0.8 each by 0.1.

Fig. 5 is a view showing the result of calculating an electromechanical coupling coefficient k^2 when a standardized electrode thickness (h/λ) is 0.01. In the drawing, an ordinate indicates an electromechanical coupling coefficient k^2 ; and an abscissa a cut angle θ of the LT substrate as in the case shown in Fig. 4. Fig. 5 shows the results of calculation made by changing the duty ratio (w/p) based on the same values as those shown in Fig. 4.

The results of calculation shown in Figs. 4 and 5 are based on the methods of analysis using discrete Green function respectively described in, for example, a document: pp. 649 to 654, "Recent Studies on Acoustic Wave Device Technology-Committee Report-, March, 1995, by Acoustic Wave Device Technology 150th Committee of Japan Society for the Promotion of Science (referred to as a document 4, hereinafter), a document: pp. 786 to 791 of the same (document 5, hereinafter), and a document: pp. 93 to 100, 23rd EM Symposium, May, 1994 (document 6, hereinafter). The back scattering effect of a program (FEMSDA) described in the document 5 is excluded in the results of calculation.

Similarly to Figs. 4 and 5, Figs. 6 and 7 show the results of calculation each made when a standardized electrode thickness (h/λ) is 0.05. The value 0.05 of the standardized electrode thickness (h/λ) is used relatively frequently in the SAW device of a GHz band.

Referring to Fig. 6, a cut angle θ with respect to a minimum attenuation constant α is shown to be larger than

that shown in Fig. 4. In Fig. 7, however, if a cut angle θ is selected for a smaller attenuation constant α , an electromechanical coupling coefficient k^2 is smaller. In other words, as shown in Fig. 6, an attenuation constant α takes a minimum value when a cut angle θ is about 38° . But an electromechanical coupling coefficient k^2 takes a larger value when a cut angle θ is lower than 38° .

Similarly to Figs. 4 and 5, or Figs. 6 and 7, Figs. 8 and 9 show the results of calculation each made when a standardized electrode thickness (h/λ) is 0.075. Referring to Fig. 8, a cut angle θ with respect to a minimum attenuation constant α is shown to be larger than that shown in Fig. 6. An attenuation constant α is minimum when a cut angle θ is about 39° . In Fig. 9, however, if a cut angle θ is selected for a smaller attenuation constant α , an electromechanical coupling coefficient k^2 is smaller. In other words, an electromechanical coupling coefficient k^2 takes a larger value when a cut angle θ is lower than 39° .

Similarly to Figs. 4 and 5, Figs. 6 and 7, or Figs. 8 and 9, Figs. 10 and 11 show the results of calculation each made when a standardized electrode thickness (h/λ) is 0.1. Referring to Fig. 10, a cut angle θ with respect to a minimum attenuation constant α is shown to be larger than that shown in Fig. 8. An attenuation constant α is minimum when a cut angle θ is about 40° . In Fig. 11, however, if a cut angle θ is selected for a smaller attenuation constant α , an electromechanical coupling constant k^2 is smaller. In other words, an electromechanical coupling coefficient k^2 takes a larger value when a cut angle θ is lower than 40° .

In Fig. 6, for example, if a duty ratio (w/p) is 0.5, an attenuation constant α takes a minimum value substantially equal to 0 when a cut angle θ is about 38° . However, in the case of the calculation result for the conventional acoustic wave apparatus of such a type, shown

in Fig. 1, if a standardized electrode thickness (h/λ) is 0.05, an attenuation constant α takes a minimum value equal to 0 when a cut angle θ is about 40° . This is attributed to the fact that the calculation result of Fig. 1 is for the ladder surface acoustic wave filter according to the document 1, and is different from the calculation result for the acoustic wave apparatus constructed by arraying the electrode fingers at an endless cycle.

Fig. 12 shows the pattern of a mode-coupled SAW resonant filter, used to determine the effects of the calculation results shown in Figs. 4 to 11 on the SAW filter. In the drawing, a reference numeral 5 denotes an input side IDT. There are 31 electrode fingers 3 provided. A reference numeral 6 denotes an output side IDT. Two output sides IDT 6 are electrically connected in parallel with each other. One side of the output side IDT 6 has 18 electrode fingers 3, while the other side has 20 electrode fingers 3. A reference numeral 9 denotes a grating reflector, which has 120 electrode fingers (i.e., strips) 10 in one side. The line widths of the electrode fingers 3 of the input and output side IDT 5 and 6 are all equal to one another at w_i , and also arraying cycles all equal to one another at p_i .

The arraying cycle p_g of the electrode fingers 10 of the grating reflector 9 shown in Fig. 12 is set at $p_g = 1.0251 p_i$, different from those of the input and output side IDT 5 and 6. The duty ratio (w_g/p_g) of the electrode fingers 10 of the grating reflector 9 is equal to that (w_i/p_i) of the electrode fingers 3 of each of the input and output side IDT 5 and 6. Hereinafter, these duty ratios (w_i/p_i) and (w_g/p_g) are generically referred to as a duty ratio (w/p).

Distances D_1 and D_2 are respectively $2.5 p_i$ and $0.25 p_i$. A maximum intersection width is $360 \mu\text{m}$.

Fig. 13 shows the result of calculating a minimum insertion loss value for the SAW filter shown in Fig. 12.

Specifically, Fig. 13 shows the results of calculation made by changing duty ratios (w/p) from 0.5 to 0.7 each by 0.1, when a standardized electrode thickness (h/λ) is 0.05 for each of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9.

For the calculation, for example, a document: pp. 185 to 205, "Acoustic Wave Device Technology Handbook", Nov. 1991, by Acoustic Wave Device Technology 150th Committee of Japan Society for the Promotion of Science (referred to as a document 7, hereinafter) is available. In the described case, specifically, a 2nd equivalent circuit model by Smith described therein (Fig. 3.76, p. 188 of the document 7) is used for the input and output side IDT 5 and 6.

For the grating reflector 9, for example, a document: pp. 206 to 227, "Acoustic Wave Device Technology Handbook", Nov. 1991, by Acoustic Wave Device Technology 150th Committee of Japan Society for the Promotion of Science (referred to as a document 8, hereinafter) is available. In the described case, specifically, a distributed constant equivalent circuit described therein (right side of Fig. 3.134, p. 221 of the document 8) is used.

The change of a cut angle θ or a duty ratio (w/p) causes a change in the propagation velocity V_s of SAW. In the described case, however, calculation is made by changing an arraying cycle p_i in such a way as to set a center frequency f_0 of each of the input and output side IDT 5 and 6 equal to 965MHz. In addition, the calculation is made by taking into consideration not only the changes of an attenuation constant α and an electromechanical coupling coefficient k^2 , but also the changes of material constants for the SAW propagation velocity V_s , a capacitance C_0 , a reflection coefficient C_1 , and so on.

Referring to Fig. 13, a value of insertion loss is shown to be minimum when a cut angle θ is about 38° , which is smaller than that used in the conventional acoustic wave

apparatus of such a type when a cut angle θ is 36° or 42° . Referring to Fig. 6, an attenuation constant α is shown to be minimum when a cut angle θ is 38° . This explains why the value of insertion loss is minimum when the cut angle θ is about 38° . It can therefore be understood that the attenuation constant α greatly affects the amount of insertion loss.

Fig. 14 shows the result of calculating feedthrough power for the SAW filter shown in Fig. 12. Specifically, Fig. 14 shows the results of calculation made by changing cut angles θ to 36° , 38° and 42° , when a standardized electrode thickness (h/λ) of each of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is 0.05, and a duty ratio (w/p) is 0.7.

In addition, the calculation is made by assuming that when a cut angle θ is 36° , an acoustic velocity V_s is 4083.4 (m/s), an attenuation constant α 0.01749 (dB/ λ), a capacitance C_0 304 (pF/m) per electrode finger, and an electromechanical coupling coefficient k^2 11.7 %; when a cut angle θ is 38° , an acoustic velocity V_s is 4085.6 (m/s), an attenuation constant α 8×10^{-6} (dB/ λ), a capacitance C_0 304 (pF/m) per electrode finger, and an electromechanical coupling coefficient k^2 11.4 %; and when a cut angle θ is 42° , an acoustic velocity V_s is 4088.3 (m/s), an attenuation constant α 0.00833 (dB/ λ), a capacitance C_0 302 (pF/m) per electrode finger, and an electromechanical coupling coefficient k^2 11.0 %.

As shown in Fig. 14, feedthrough power is only slightly lower when the cut angle θ is 36° compared with that when the cut angle θ is 38° . However, when the cut angle θ is 42° , feedthrough power is lower by 0.1 dB or more compared with that when the cut angle θ is 38° . As shown in Fig. 6, an attenuation constant α is larger when the cut angle θ is 36° or 42° , compared with that when the cut angle θ is 38° . As shown in Fig. 7, an

electromechanical coupling coefficient k^2 is larger when the cut angle θ is 36° , compared with that when the cut angle θ is 38° . When the cut angle θ is 42° , an electromechanical coupling coefficient k^2 is smaller compared with that when the cut angle θ is 38° . The only slightly lower level of the feedthrough power when the cut angle θ is 36° compared with that when the cut angle θ is 38° can be attributed to the fact that when the cut angle θ is 36° , not only the attenuation constant α but also the electromechanical coupling coefficient k^2 are larger than those when the cut angle θ is 38° . The lower level of the feedthrough power by 0.1 dB or more when the cut angle θ is 42° compared with that when the cut angle θ is 38° can be attributed to the fact that when the cut angle θ is 42° , the attenuation constant α is larger than that when the cut angle θ is 38° , but the electromechanical coupling coefficient k^2 is smaller. Accordingly, it can be understood that the electromechanical coupling coefficient k^2 also affects the amount of insertion loss greatly.

As can be understood from Fig. 7, the increase of the duty ratio (w/p) brings about a larger electromechanical coupling coefficient k^2 , reducing the amount of insertion loss and widening a pass band width. Even if the larger attenuation constant α increases the amount of loss following propagation, a corresponding increase if made in the electromechanical coupling coefficient k^2 results in a reduction in the amount of insertion loss.

As shown in Fig. 4, the attenuation constant α takes a minimum value when the cut angle θ is about 37° and, by setting the cut angle θ in the range of 34° to 40° , the attenuation constant α can be limited to 0.005 (dB/ λ). In addition, as shown Fig. 6, the attenuation constant α takes a minimum value when the cut angle θ is about 38° and, by setting the cut angle θ in the range of 35° to 41° , the attenuation constant α can be limited to 0.005 (dB/ λ).

As shown in Figs. 5 and 7, when the cut angle θ is

set in the range of 34° to 41° , the cut angle θ is 36° or 42° if the duty ratio (w/p) is 0.6 or higher. The electromechanical coupling coefficient k^2 is larger than that in the conventional case having the duty ratio (w/p) of 0.5. In the case having a large standardized electrode thickness (h/λ) shown in Fig. 7, compared with that shown in Fig. 5, the electromechanical coupling coefficient k^2 is larger under equal cut angles θ and equal duty ratios (w/p). There have been no reports made hitherto regarding the result of calculating an electromechanical coupling coefficient based on consideration given to the duty ratio. Thus, in the described case, a general duty ratio 0.5 was used as a conventional duty ratio. The same applies hereinafter.

As described above, according to the first embodiment, the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of each of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ration (w/p) of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set to the value ranging from 0.6 to just below 1.0. Thus, it is possible to realize an acoustic wave apparatus with lower loss characteristics and wider band characteristics as compared with the conventional acoustic wave apparatus of such a type.

Such an advantage can be obtained not only when the input and output side IDT 5 and 6 and the grating reflector 9 all satisfy the above-described conditions, but also when only one of the components satisfies the conditions.

For example, a similar advantage can be obtained when only the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of the

electrode finger 3 of the input side IDT 5 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the input side IDT 5 is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode3 thickness of the electrode finger 3 of the output side IDT 6 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the output side IDT 6 is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when only the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of the electrode finger 10 of the grating reflector 9 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 10 of the grating reflector 9 is set to the value ranging from 0.6 to just below 1.0.

In addition, the foregoing advantage can be obtained not only when all the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9 satisfy the conditions, but also when a part of the electrode fingers satisfies the conditions.

For example, a similar advantage can be obtained when a part of the electrode fingers 3 of the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set

to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when a part of the electrode fingers 3 of the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , and the electrode thickness of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of a part of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

Furthermore, the foregoing advantage can be obtained not only when all portions of a part of the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9 satisfy the conditions, but also when only a portion thereof satisfies the conditions.

For example, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of a portion of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the

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output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of a portion of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when only a portion of a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 34° to 41° , the electrode thickness of a portion of a part of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.01 to 0.05 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

[Second Embodiment]

As shown in Fig. 6, the attenuation constant α takes a minimum value when the cut angle θ is about 38° and, by setting the cut angle θ in the range of 35° to 41° , the attenuation constant α can be limited to 0.005 (dB/ λ). In addition, as shown in Fig. 8, the attenuation constant α takes a minimum value when the cut angle θ is about 39° and, by setting the cut angle θ in the range of 36° to 42° , the attenuation constant α can be limited to 0.005 (dB/ λ).

As shown in Figs. 7 and 9, when the cut angle θ is set in the range of 35° to 42° , and the duty ratio (w/p) is 0.6 or higher, the electromechanical coupling coefficient k^2 is larger than that in the conventional case in which the cut angle θ is 36° and the duty ratio (w/p) is 0.5. In the case having a large standardized electrode thickness (h/ λ) shown in Fig. 9, compared with that shown in Fig. 7, the electromechanical coupling coefficient k^2 is larger

under equal cut angles θ and equal duty ratios (w/p).

As described above, according to the second embodiment, the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of each of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set to the value ranging from 0.6 to just below 1.0. Thus, it is possible to realize an acoustic wave apparatus with lower loss characteristics and wider band characteristics as compared with the conventional acoustic wave apparatus of such a type.

Such an advantage can be obtained not only when the input and output side IDT 5 and 6 and the grating reflector 9 all satisfy the foregoing conditions, but also when only one of the components satisfies the conditions.

For example, a similar advantage can be obtained when only the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of the electrode finger 3 of the input side IDT 5 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the input side IDT 5 is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of the electrode finger 3 of the output side IDT 6 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the output side IDT 6 is set to the value ranging from 0.6 to

just below 1.0.

Likewise, a similar advantage can be obtained when only the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of the electrode finger 10 of the grating reflector 9 is set in the range of 0.05 to 0.07 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 10 of the grating reflector 9 is set to the value ranging from 0.6 to just below 1.0.

In addition, the foregoing advantage can be obtained not only when all the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9 satisfy the conditions, but also when a part of the electrode fingers satisfies the conditions.

For example, a similar advantage can be obtained when a part of the electrode fingers 3 of the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when a part of the electrode fingers 3 of the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the

LT substrate is set in the range of 35° to 42° , the electrode thickness of a part of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

Furthermore, the foregoing advantage can be obtained not only when all portions of a part of the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9 satisfy the conditions, but also when only a portion thereof satisfies the conditions.

For example, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of a portion of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of a portion of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when only a portion of a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 35° to 42° , the electrode thickness of a portion of a part

of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.05 to 0.075 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

[Third Embodiment]

As shown in Fig. 8, the attenuation constant α takes a minimum value when the cut angle θ is about 39° and, by setting the cut angle θ in the range of 36° to 42° , the attenuation constant α can be limited to 0.005 (dB/ λ). In addition, as shown in Fig. 10, the attenuation constant α takes a minimum value when the cut angle θ is about 40° and, by setting the cut angle θ in the range of 37° to 43° , the attenuation constant α can be limited to 0.005 (dB/ λ).

As shown in Figs. 9 and 11, when the cut angle θ is set in the range of 36° to 43° , and the duty ratio (w/p) is 0.6 or higher, the electromechanical coupling coefficient k^2 is larger than that in the conventional case in which the cut angle θ is 36° and the duty ratio (w/p) is 0.5. In the case having a large standardized electrode thickness (h/ λ) shown in Fig. 11, compared with that shown in Fig. 9, the electromechanical coupling coefficient k^2 is larger under equal cut angles θ and equal duty ratios (w/p).

As described above, according to the third embodiment, the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of each of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode fingers 3 and 10 respectively of the input and output side IDT 5 and 6 and the grating reflector 9 is set to the value ranging from 0.6 upto just below 1.0. Thus, it is possible to realize an acoustic wave apparatus with lower loss characteristics and wider band characteristics as compared

with the conventional acoustic wave apparatus of such a type.

Such an advantage can be obtained not only when the input and output side IDT 5 and 6 and the grating reflector 9 all satisfy the foregoing conditions, but also when only one of the components satisfies the conditions.

For example, a similar advantage can be obtained when only the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of the electrode finger 3 of the input side IDT 5 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the input side IDT 5 is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of the electrode finger 3 of the output side IDT 6 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 3 of the output side IDT 6 is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when only the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of the electrode finger 10 of the grating reflector 9 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of the electrode finger 10 of the grating reflector 9 is set to the value ranging from 0.6 to just below 1.0.

In addition, the foregoing advantage can be obtained not only when all the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9 satisfy

the conditions, but also when a part of the electrode fingers satisfies the conditions.

For example, a similar advantage can be obtained when a part of the electrode fingers 3 of the input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when a part of the electrode fingers 3 of the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a part of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

In addition, the foregoing advantage can be obtained not only when all portions of a part of the electrode fingers of the input and output side IDT 5 and 6 and the grating reflector 9, but also when only a portion thereof satisfies the conditions.

For example, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the

input side IDT 5 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a portion of a part of the electrode fingers 3 of the input side IDT 5 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Similarly, a similar advantage can be obtained when only a portion of a part of the electrode fingers 3 of the output side IDT 6 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a portion of a part of the electrode fingers 3 of the output side IDT 6 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 3 thereof is set to the value ranging from 0.6 to just below 1.0.

Likewise, a similar advantage can be obtained when only a portion of a part of the electrode fingers 10 of the grating reflector 9 satisfies the conditions, i.e., when the cut angle θ of the LT substrate is set in the range of 36° to 43° , the electrode thickness of a portion of a part of the electrode fingers 10 of the grating reflector 9 is set in the range of 0.075 to 0.1 with respect to a wavelength of SAW, and the duty ratio (w/p) of a portion of a part of the electrode fingers 10 thereof is set to the value ranging from 0.6 to just below 1.0.

The invention has been described by taking the example of the mode-coupled SAW resonant filter shown in Fig. 12. However, the invention is not limited to such, and a similar advantage can be obtained even when a given number of IDT units other than 3 is prepared. Further, the invention is similarly advantageous even when it is applied to a so-called transversal filter having a multielectrode structure or the simply structured SAW filter shown in Fig.

2.

In addition, in the foregoing cases, the arraying cycles of the electrode fingers 3 were all similar. However, the invention is similarly advantageous even when the arraying cycles are partially or entirely changed. A similar advantage can also be obtained even in the case where there is a floating electrode in the IDT or floating electrodes present at different positions in the IDT are electrically connected to each other.

Furthermore, the present invention is advantageous not only for the SAW filter but also for all the other types of SAW devices including IDT having a function of conversion for the electric signal of a one terminal pair SAW resonator, a SAW delay line, a SAW dispersed delay line, a SAW convolver or the like with LSAW and SSBW. The invention is also advantageous for all acoustic wave apparatus using such SAW devices.

Industrial Applicability

As apparent from the foregoing, the acoustic wave apparatus of the invention is suitable for realizing a characteristic of smaller loss and a wider band than those in the conventional art.

WHAT IS CLAIMED IS:

1. An acoustic wave apparatus comprising:
a piezoelectric substrate mainly containing tantalic acid lithium; and
an interdigital transducer including a conductor formed on said substrate,
wherein a surface rotated in a range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.01 to 0.05, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

2. An acoustic wave apparatus comprising:
a piezoelectric substrate mainly containing tantalic acid lithium; and
an interdigital transducer including a conductor formed on said substrate,
wherein a surface rotated in a range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.05 to 0.075, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode is set to the value ranging from 0.6 to just below 1.0.

3. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalic acid lithium; and

an interdigital transducer including a conductor
formed on said substrate,

wherein a surface rotated in a range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.075 to 0.1, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

4. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalic acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting at least a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.01 to 0.05, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

5. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalum acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting at least a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.05 to 0.075, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

6. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalum acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting at least a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.075 to 0.1, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

7. An acoustic wave apparatus comprising:
a piezoelectric substrate mainly containing tantalic acid lithium; and

an interdigital transducer including a conductor formed on said substrate,

wherein a surface rotated in a range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting a part of said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.01 to 0.05, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

8. An acoustic wave apparatus comprising:
a piezoelectric substrate mainly containing tantalic acid lithium; and

an interdigital transducer including a conductor formed on said substrate,

wherein a surface rotated in a range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting a part of said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.05 to 0.75, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

9. An acoustic wave apparatus comprising:
a piezoelectric substrate mainly containing tantalic

acid lithium; and

an interdigital transducer including a conductor formed on said substrate,

wherein a surface rotated in a range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of an electrode finger constituting a part of said interdigital transducer by a wavelength λ of a surface acoustic wave is set in a range of 0.075 to 0.1, and a duty ratio (w/p) of the electrode finger decided based on a width w and an arraying cycle p of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

10. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalic acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 34° to 41° from a crystal Y axis around a crystal X axis of the tantalic acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.01 to 0.05, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arraying cycle p of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

11. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalic

acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 35° to 42° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.05 to 0.075, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arranging cycle of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

12. An acoustic wave apparatus comprising:

a piezoelectric substrate mainly containing tantalum acid lithium;

an interdigital transducer including a conductor formed on said substrate; and

a reflector including a conductor formed on said substrate,

wherein a surface rotated in a range of 36° to 43° from a crystal Y axis around a crystal X axis of the tantalum acid lithium is set as a surface of said substrate, a standardized electrode thickness (h/λ) obtained by standardizing a thickness h of a part of an electrode finger constituting a part of said reflector by a wavelength λ of a surface acoustic wave is set in a range of 0.075 to 0.1, and a duty ratio (w/p) of a part of the electrode finger decided based on a width w and an arraying cycle p of a part of the electrode finger is set to the value ranging from 0.6 to just below 1.0.

[illegible][illegible]

FIG. 1

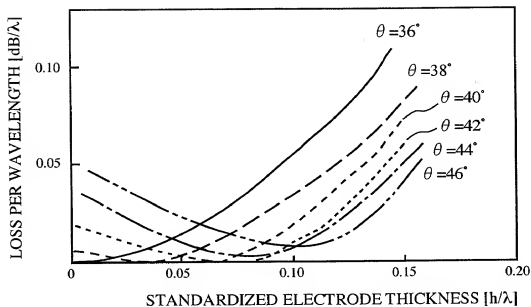


FIG. 2

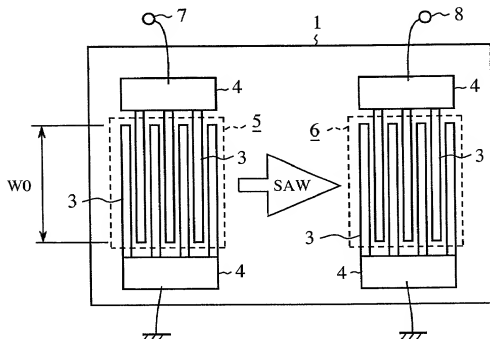


FIG.3

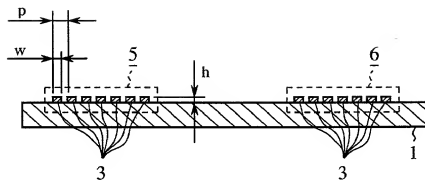


FIG.4

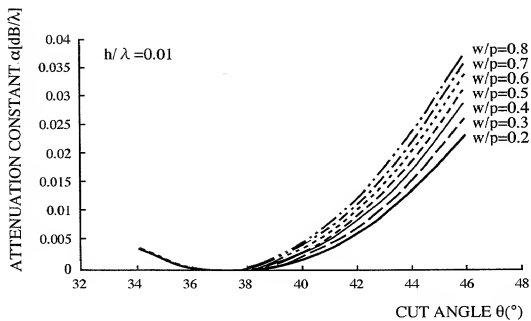


FIG.5

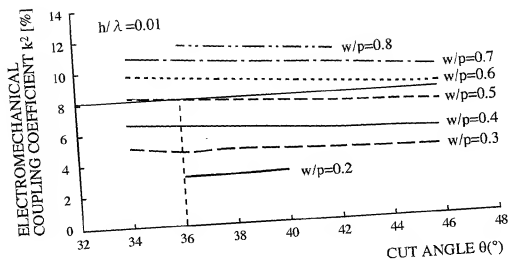


FIG.6

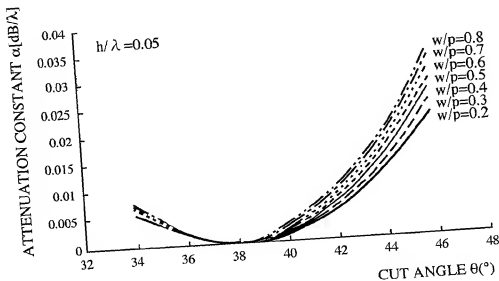


FIG.7

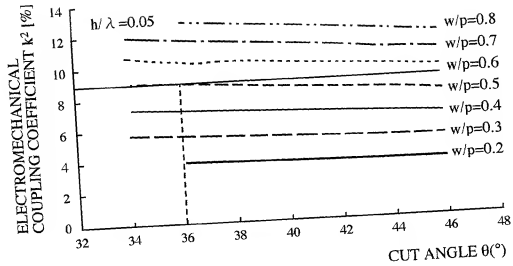


FIG.8

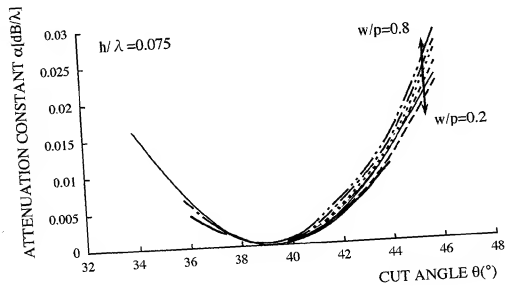


FIG.9

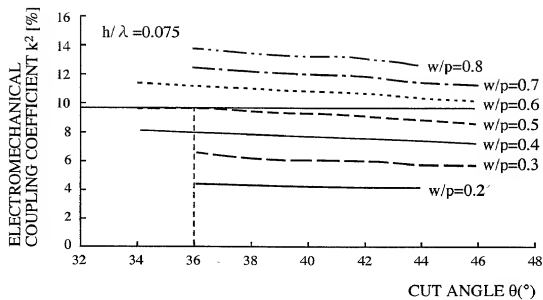


FIG.10

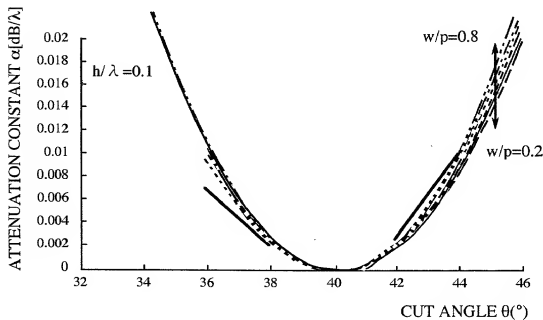


FIG.11

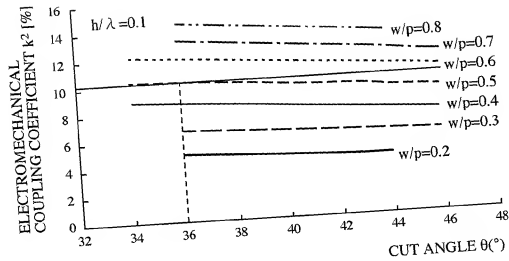


FIG.12

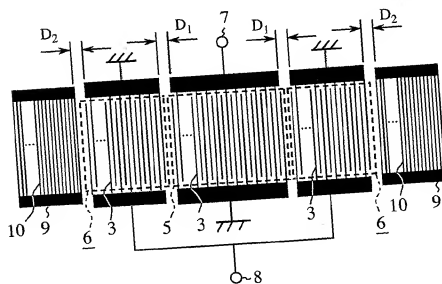


FIG.13

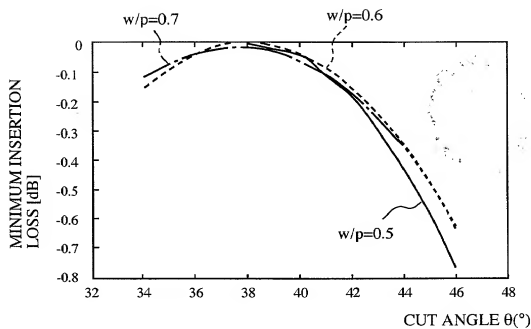
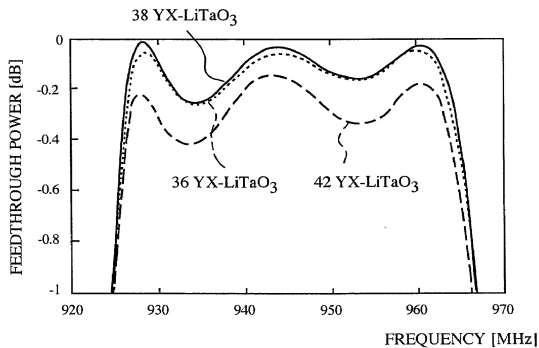


FIG.14



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Declaration and Power of Attorney For Patent Application

特許出願宣言書及び委任状

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As a below named inventor, I hereby declare that:

私の住所、私書箱、国籍は下記の私の氏名の後に記載された通りです。

My residence, post office address and citizenship are as stated next to my name.

下記の名称の発明に関して請求範囲に記載され、特許出願している発明内容について、私が最初かつ唯一の発明者（下記の氏名が一つの場合）もしくは最初かつ共同発明者であると（下記の名称が複数の場合）信じています。

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

"ACOUSTIC WAVE APPARATUS"

上記発明の明細書（下記の欄でx印がついていない場合は、本書に添付）は、

the specification of which is attached hereto unless the following box is checked:

☐ 月 日に提出され、米国出願番号または特許協定条約国際出願番号を _____ とし、
(該当する場合) _____ に訂正されました。

☒ was filed on October 18, 2000
as United States Application Number or
PCT International Application Number
PCT/JP00/07239 and was amended on
_____ (if applicable).

私は、特許請求範囲を含む上記訂正後の明細書を検討し、内容を理解していることをここに表明します。

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

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Prior Foreign Application(s)

 外国での先行出願
 11-325799

 (Number)
 (番号)

Japan

 (Country)
 (国名)

16/November/1999

 (Day/Month/Year Filed)
 (出願年月日)

Priority Not Claimed

優先権主張なし

☐

 (Number)
 (番号)

 (Country)
 (国名)

 (Day/Month/Year Filed)
 (出願年月日)

☐

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 (Application No.)
 (出願番号)

 (Filing Date)
 (出願日)

 (Application No.)
 (出願番号)

 (Filing Date)
 (出願日)

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 (Application No.)
 (出願番号)

 (Filing Date)
 (出願日)

 (Status: Patented, Pending, Abandoned)
 (現況: 特許許可済、係属中、放棄済)

 (Application No.)
 (出願番号)

 (Filing Date)
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 (Status: Patented, Pending, Abandoned)
 (現況: 特許許可済、係属中、放棄済)

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I hereby claim the benefit under Title 36, United States Code, Section 119(c) of any United States provisional application(s) listed below.

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として、下記の者を指名いたします。(弁理士、または代理人
の氏名及び登録番号を明記のこと)

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国籍	Citizenship		
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同第11発明者の署名	日付	Eleventh Inventor's signature	Date
住所	Residence		
国籍	Citizenship		
郵便の宛先	Post Office Address		